

SILICON CARBIDE DEVICES

Session D: Oral presentations

Chair:

M. Brezeanu, Honeywell Romania SRL, Bucharest,
Romania

M. Bazu, IMT Bucharest, Romania

- D.2** *THE LATERAL SUPERJUNCTION PSOI LIGHT AND LDMOSFET*, **M. Antoniou**, **E. Kho Ching Tee***, **S.J. Pilkington***, **D. Kumar Pal***, **F. Udrea**, **A.D. Hoelke***, Univ. of Cambridge, United Kingdom, *X-FAB Sarawak Sdn Bhd, Sarawak, Malaysia.
- D.3** *A MODEL OF THE VOLTAGE BARRIER IN THE CHANNEL OF 4H-SiC NORMALLY-OFF JFET's*, **L. Di Benedetto**, **S. Bellone**, Univ. of Salerno, Italy.
- D.4** *SiC SCHOTTKY DIODE SURGE CURRENT ANALYSIS AND APPLICATION DESIGN USING BEHAVIORAL SPICE MODELS*, **V. Banu**, **P. Godignon**, **X. Jorda**, **M. Alexandru**, **J. Millan**, IMB-CNM, CSIC, Barcelona, Spain.
- D.5** *MODELLING 2DEG CHARGES IN AlGaIn/GaN HETEROSTRUCTURES*, **G. Longobardi**¹, **F. Udrea**¹, **S. Sque**², **J. Croon**², **F. Hurkx**², **E. Napoli**³, **J. Sonsky**², ¹Cambridge Univ., United Kingdom, ²NXP Semiconductors, Eindhoven, The Netherlands, ³DIBET, Univ. of Naples Federico II, Italy.

D.6 *HYDROGEN SENSOR BASED ON SILICON CARBIDE (SiC) MOS CAPACITOR*, **B. Ofrim, F. Udrea*, G. Brezeanu, A. Pei-Shan Hsieh***, Univ. “Politehnica” of Bucharest, Romania, *Cambridge Univ., United Kingdom.

11:00–11:30 COFFEE BREAK
